

SEMIPONT™ 6

3-Phase Bridge Rectifier + IGBT braking chopper

SKD146/..L105

Features

- Compact design
- Two screws mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High surge currents
- Up to 1600V reverse voltage
- IGBT Trench4 inside; max $T_j=175^{\circ}\text{C}$
- CAL4F diode inside, max $T_j=175^{\circ}\text{C}$
- $I_{CM}/I_{FM} = 3 \times I_{C,nom}/I_{F,nom}$
- Rectifier diode, max $T_j=150^{\circ}\text{C}$

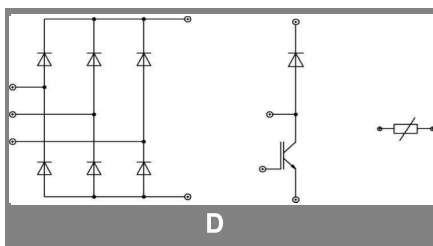
Typical Applications*

- DC drives
- Controlled filed rectifiers for DC motors
- Controlled battery charger

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_D = 120 \text{ A}$ (maximum value for continuous operation) ($T_s = 70^{\circ}\text{C}$)
1300	1200	SKD146/12-L105
1700	1600	SKD146/16-L105

Absolute Maximum Ratings		$T_s = 25^{\circ}\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
Bridge - Rectifier			
I_D	$T_s = 85^{\circ}\text{C}$; inductive load	140	A
I_{FSM}/I_{TSM}	$t_p = 10 \text{ ms}$; $\sin 180^{\circ}$; T_{jmax}	1250	A
i^2t	$t_p = 10 \text{ ms}$; $\sin 180^{\circ}$; T_{jmax}	7800	A ² s
IGBT - Chopper			
V_{CES}/V_{GES}	$T_s = 25 (70)^{\circ}\text{C}$	1200 / 20	V
I_C	$T_s = 25 (70)^{\circ}\text{C}$	110 (80)	A
I_{CM}	$t_p = 1 \text{ ms}$; $T_s = ^{\circ}\text{C}$	315	A
Freewheeling - CAL Diode			
V_{RRM}	$T_s = 25 (70)^{\circ}\text{C}$	1200	V
I_F	$T_s = 25 (70)^{\circ}\text{C}$	90 (60)	A
I_{FM}	$t_p = 1 \text{ ms}$; $T_s = ^{\circ}\text{C}$	300	A
T_{vj}	Diode & IGBT (Thyristor)	- 40 ... + 175 (0 ... + 125)	$^{\circ}\text{C}$
T_{stg}		- 40 ... + 125	$^{\circ}\text{C}$
T_{solder}	terminals, 10 s	260	$^{\circ}\text{C}$
V_{isol}	a.c. (50) Hz, RMS 1 min. / 1 s	3000 / 3600	V

Characteristics		$T_s = 25^{\circ}\text{C}$, unless otherwise specified		
Symbol	Conditions	min.	typ.	max. Units
Diode - Rectifier				
V_{TO} / r_t	$T_j = 125^{\circ}\text{C}$		0,8 / 4	V / mΩ
$R_{th(j-s)}$	per diode			0,8 K/W
IGBT - Chopper				
$V_{CE(sat)}$	$I_C = 105 \text{ A}$, $T_j = 25^{\circ}\text{C}$; $V_{GE} = 15 \text{ V}$		1,85	2,1 V
$R_{th(j-s)}$	per IGBT		0,46	K/W
$t_{d(on)} / t_r$	valid for all values:		97 / 185	ns
$t_{d(off)} / t_f$	$V_{CC} = 600 \text{ V}$; $V_{GE} = 15 \text{ V}$; $I_C = 105 \text{ A}$; $T_j = 150^{\circ}\text{C}$;		443 / 82	ns
$E_{on}+E_{off}$	$T_j = 150^{\circ}\text{C}$; $R_G = 3 \Omega$; inductive load		47,5	mJ
CAL - Diode - Freewheeling				
$V_{T(TO)} / r_t$	$T_j = 150^{\circ}\text{C}$		0,9 / 12,5	1,1 / 13,7 V / mΩ
$R_{th(j-s)}$	per diode		0,75	K/W
I_{RRM}	valid for all values:			A
Q_{rr}	$I_F = 140 \text{ A}$; $V_R = - -600 \text{ V}$; $di_F/dt = - \text{A}/\mu\text{s}$			μC
E_{off}	$V_{GE} = 0 \text{ V}$; $T_j = 150^{\circ}\text{C}$			mJ
Temperature Sensor				
R_{TS}	$T = 25 (100)^{\circ}\text{C}$;		1000 (1670)	Ω
Mechanical data				
M_S	mounting Torque	2,55	3,45	Nm



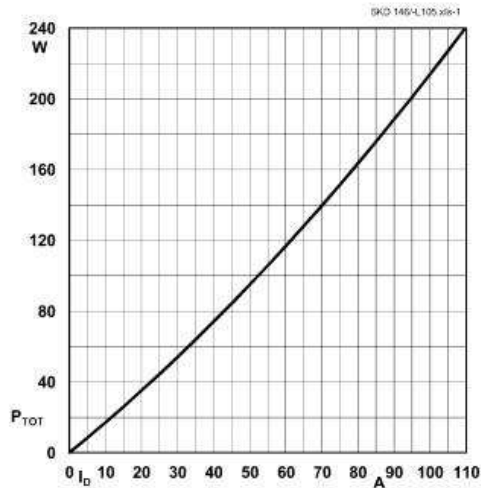


Fig. 1 Power dissipation per module vs. output current

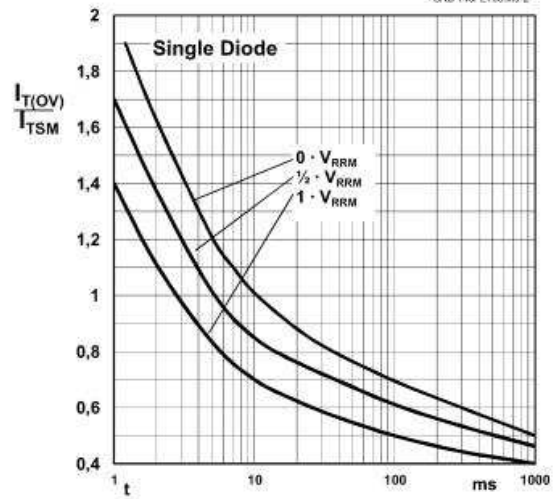


Fig. 2 Surge overload current vs. time

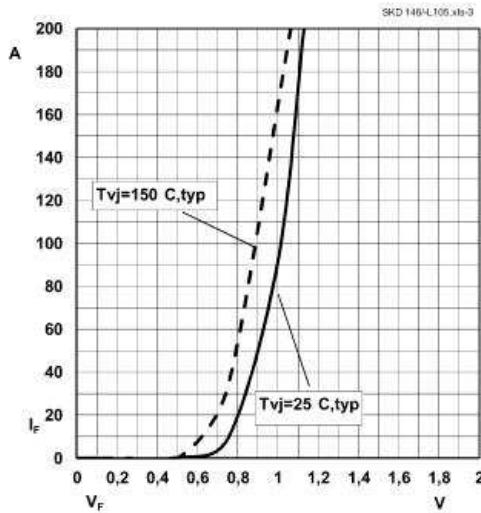


Fig. 3 Forward characteristic of single rectifier diode

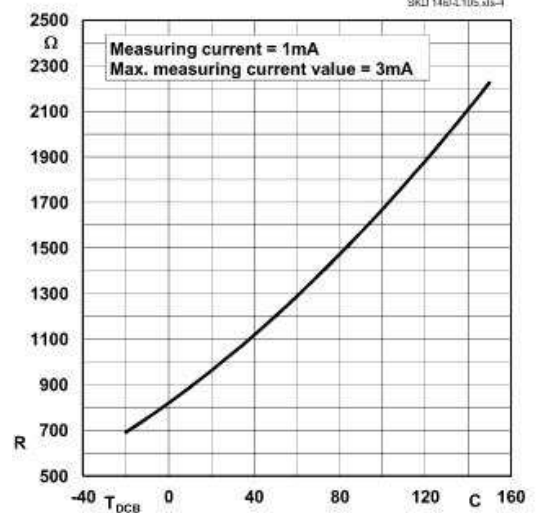


Fig. 4 Temperature sensor characteristic

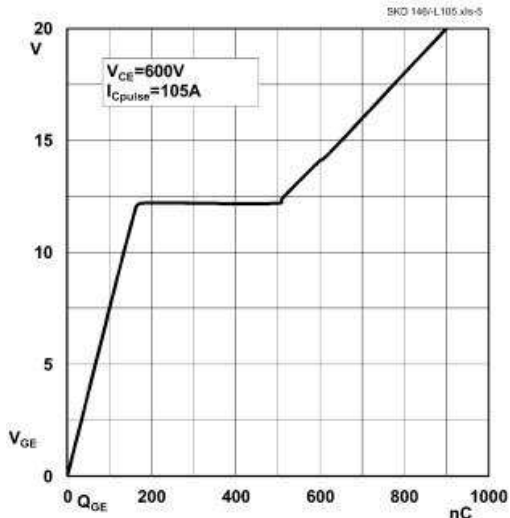


Fig. 5 Typ. gate charge characteristic

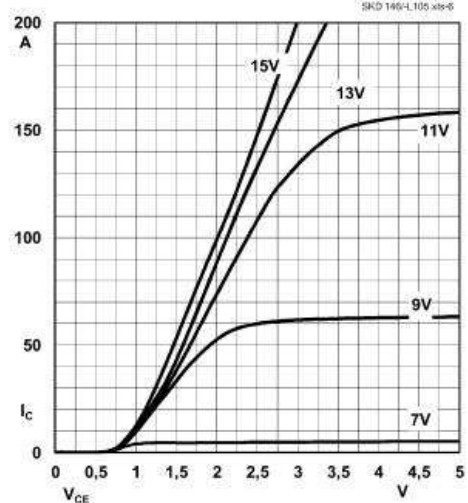
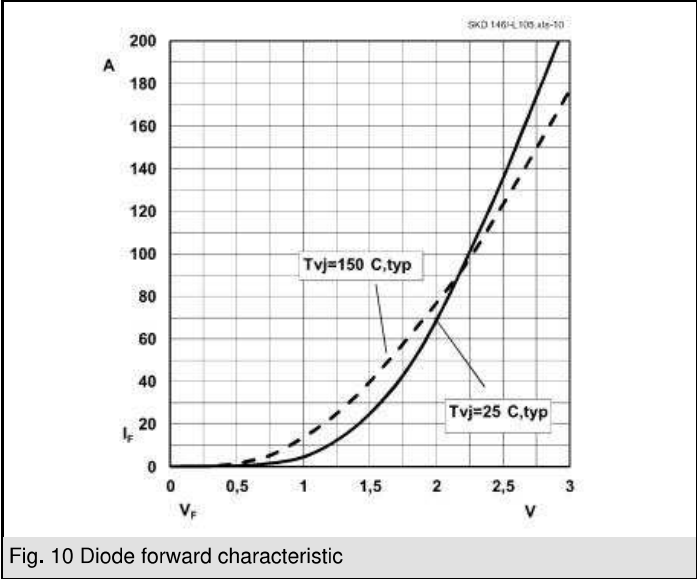
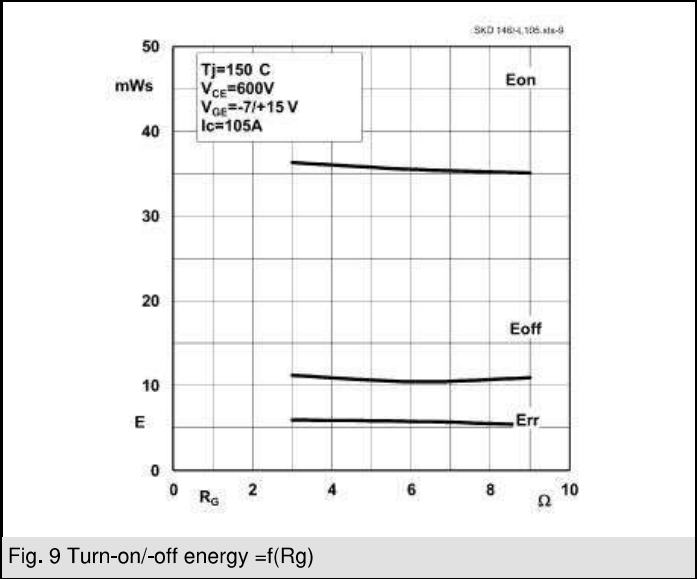
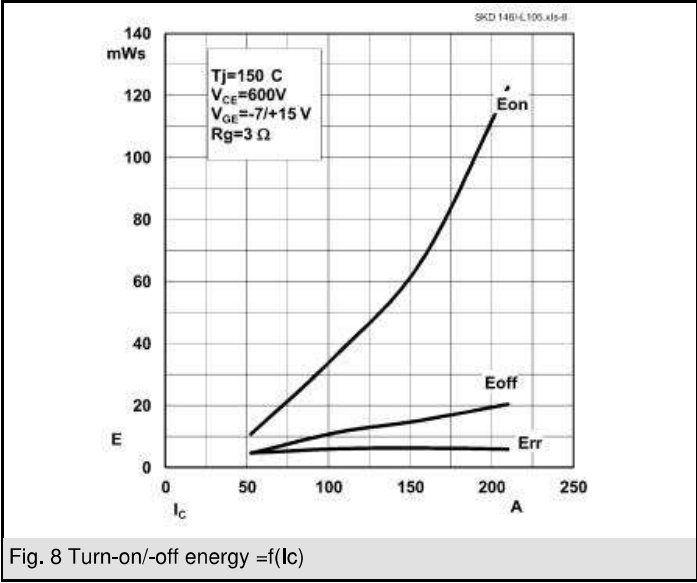
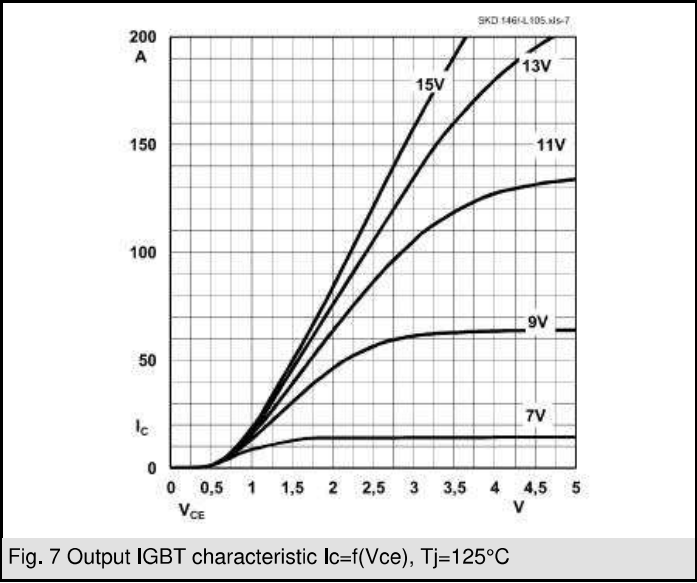
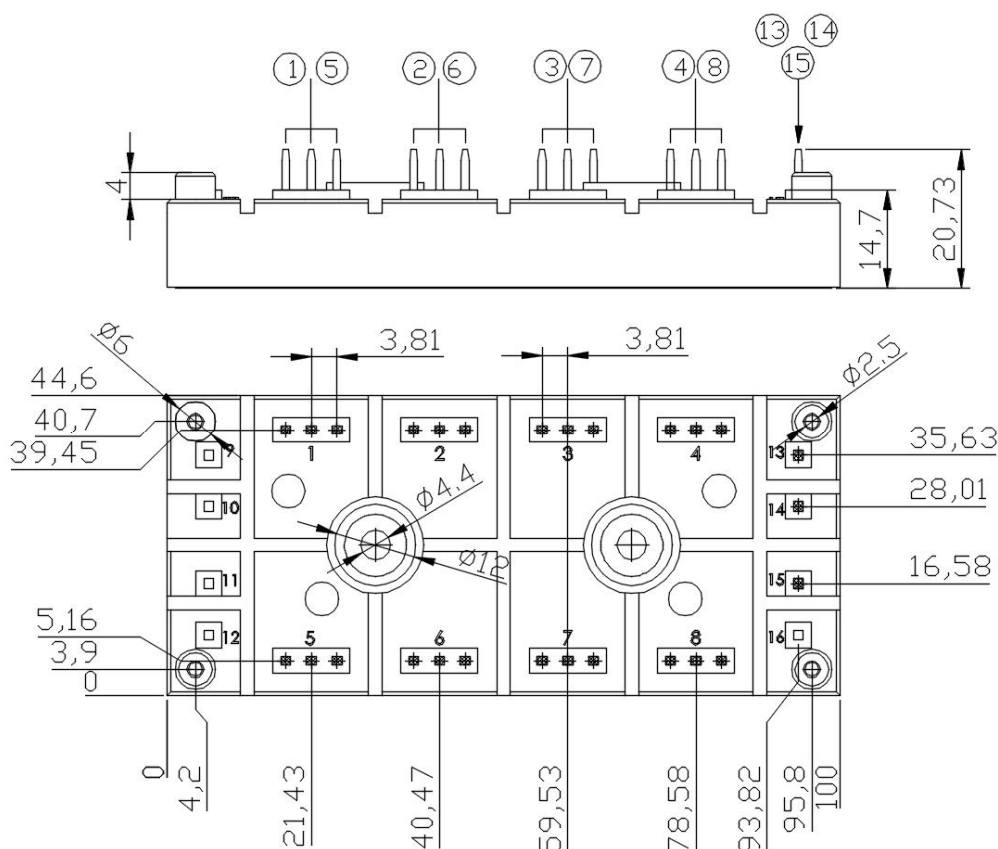
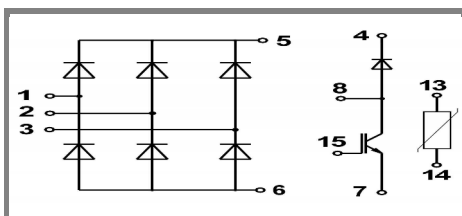


Fig. 6 Output IGBT characteristic $I_c=f(V_{ce})$, $T_j=25^\circ\text{C}$





Case G 60



Case G 60

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

*IMPORTANT INFORMATION AND WARNINGS

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